**Product data sheet** 

## 1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 2. Features and benefits

- Trench MOSFET technology
- Low threshold voltage
- Very fast switching
- Enhanced power dissipation capability of 1240 mW

## 3. Applications

- · Relay driver
- High-speed line driver
- High-side loadswitch
- Switching circuits

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-20	V
V <sub>GS</sub>	gate-source voltage			-12	-	12	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	-	-3.9	Α
Static characte	Static characteristics						,
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = -4.5 V; $I_D$ = -3.1 A; $T_j$ = 25 °C		-	72	88	mΩ

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



20 V, P-channel Trench MOSFET

# 5. Pinning information

#### Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	<u> </u>	D L
2	D	drain		
3	G	gate		G V
4	S	source	TSOP6 (SOT457)	\$ 017aaa257
5	D	drain		
6	D	drain		

# 6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PMN70XP	TSOP6	plastic surface-mounted package (TSOP6); 6 leads	SOT457		

## 7. Marking

#### Table 4. Marking codes

Type number	Marking code
PMN70XP	H5

**Product data sheet** 

## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Parameter	Conditions		Min	Max	Unit
drain-source voltage	T <sub>j</sub> = 25 °C		-	-20	V
gate-source voltage			-12	12	V
drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$	[1]	-	-3.9	Α
	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-3.1	Α
	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	-2	Α
peak drain current	T <sub>amb</sub> = 25 °C; single pulse; t <sub>p</sub> ≤ 10 μs		-	-13	Α
total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	530	mW
		[1]	-	1.24	W
	T <sub>sp</sub> = 25 °C		-	4.46	W
junction temperature			-55	150	°C
ambient temperature			-55	150	°C
storage temperature			-65	150	°C
diode					1
source current	T <sub>amb</sub> = 25 °C	[1]	-	-1.2	Α
	drain-source voltage gate-source voltage drain current  peak drain current total power dissipation  junction temperature ambient temperature storage temperature	$ \begin{array}{lll} & & & & & & & \\ & & & & & \\ & & & & \\ & & & & \\ & & & \\ & & & \\ & & & \\ & $	$ \begin{array}{llllllllllllllllllllllllllllllllllll$	$ \begin{array}{c} \text{drain-source voltage} \\ \text{gate-source voltage} \\ \end{array} \begin{array}{c} T_{j} = 25  ^{\circ}\text{C} \\ \end{array} \begin{array}{c} -12 \\ \end{array} \\ \text{drain current} \\ \end{array} \begin{array}{c} V_{GS} = -4.5  \text{V};  T_{amb} = 25  ^{\circ}\text{C};  t \leq 5  \text{s} \\ \end{array} \begin{array}{c} \text{[1]} \\ -12 \\ \end{array} \\ V_{GS} = -4.5  \text{V};  T_{amb} = 25  ^{\circ}\text{C} \\ \end{array} \begin{array}{c} \text{[1]} \\ -12 \\ \end{array} \\ V_{GS} = -4.5  \text{V};  T_{amb} = 25  ^{\circ}\text{C} \\ \end{array} \begin{array}{c} \text{[1]} \\ -12 \\ \end{array} \\ \text{peak drain current} \\ \end{array} \begin{array}{c} T_{amb} = 25  ^{\circ}\text{C};  \text{single pulse};  t_{p} \leq 10  \mu\text{s} \\ \end{array} \begin{array}{c} -12 \\ \end{array} \\ \text{total power dissipation} \\ \end{array} \begin{array}{c} T_{amb} = 25  ^{\circ}\text{C};  \text{single pulse};  t_{p} \leq 10  \mu\text{s} \\ \end{array} \begin{array}{c} -12 \\ \end{array} \\ \end{array} \\ \text{In total power dissipation} \\ \end{array} \begin{array}{c} T_{amb} = 25  ^{\circ}\text{C} \\ \end{array} \begin{array}{c} \text{[2]} \\ -13 \\ \end{array} \\ \end{array} \begin{array}{c} -13 \\ \end{array} \\ \end{array} \\ \text{In total power dissipation} \\ \end{array} \begin{array}{c} T_{amb} = 25  ^{\circ}\text{C} \\ \end{array} \begin{array}{c} -13 \\ \end{array} \\ \end{array} \\ = -12 \\ \end{array} \\ \begin{array}{c} T_{amb} = 25  ^{\circ}\text{C} \\ \end{array} \begin{array}{c} -13 \\ \end{array} \\ \end{array} \\ = -12 \\ \end{array} \\ \begin{array}{c} -12 \\ \end{array} \\ \begin{array}{c} -12 \\ \end{array} \\ \end{array} \\ \begin{array}{c} -12 \\ \end{array} \\ \end{array} \\ \begin{array}{c} -12 \\ \end{array} \\ \begin{array}{c} -12 \\ \end{array} \\ \end{array} \\ \begin{array}{c} -12 \\ \end{array} \\ \begin{array}{c} -12 \\ \end{array} \\ \end{array} \\ \begin{array}{c} -12 \\ \end{array} \\ \begin{array}{c$	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$

- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

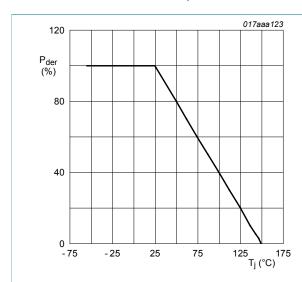


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

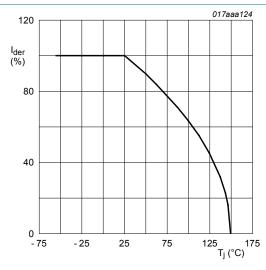


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

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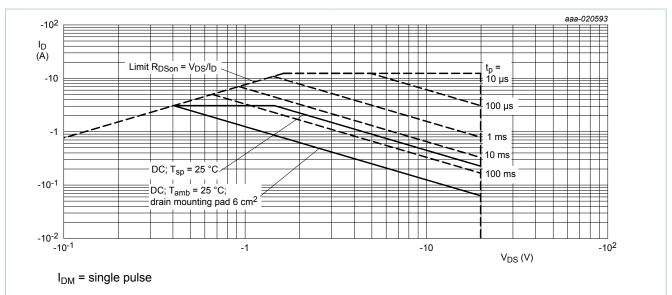


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

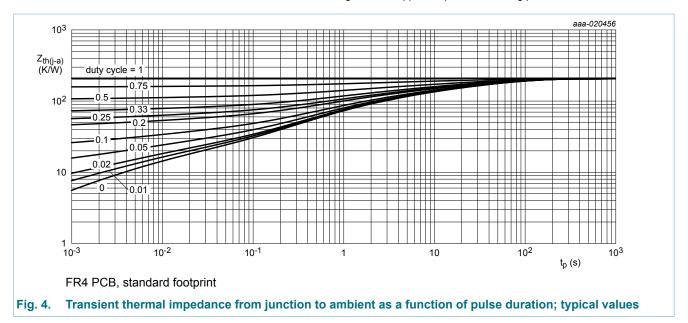
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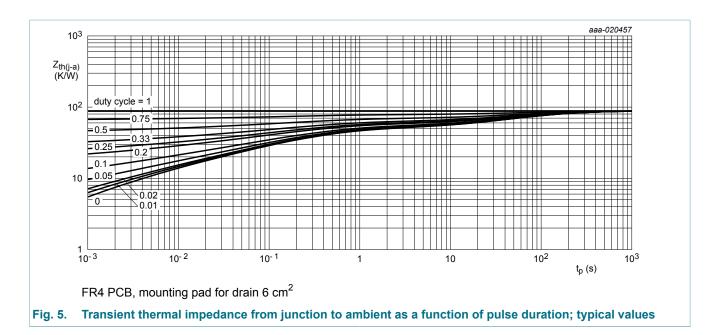
### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance		[1]	-	205	235	K/W
	from junction to ambient		[2]	-	88	101	K/W
	ambient	in free air; t ≤ 5 s	[2]	-	55	63	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	24	28	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.





20 V, P-channel Trench MOSFET

## 10. Characteristics

#### Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D$ = -250 $\mu$ A; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-20	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = -250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	-0.47	-0.65	-0.9	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = -20 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-1	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 12 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
		V <sub>GS</sub> = -12 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-100	nA
R <sub>DSon</sub>	drain-source on-state	$V_{GS}$ = -4.5 V; $I_D$ = -3.1 A; $T_j$ = 25 °C	-	72	88	mΩ
	resistance	V <sub>GS</sub> = -4.5 V; I <sub>D</sub> = -3.1 A; T <sub>j</sub> = 150 °C	-	107	130	mΩ
		V <sub>GS</sub> = -2.5 V; I <sub>D</sub> = -2.6 A; T <sub>j</sub> = 25 °C	-	88	116	mΩ
		V <sub>GS</sub> = -1.8 V; I <sub>D</sub> = -0.7 A; T <sub>j</sub> = 25 °C	-	110	170	mΩ
		V <sub>GS</sub> = -1.5 V; I <sub>D</sub> = -0.1 A; T <sub>j</sub> = 25 °C	-	150	360	mΩ
9 <sub>fs</sub>	forward transconductance	$V_{DS}$ = -10 V; $I_{D}$ = -2 A; $T_{j}$ = 25 °C	-	15	-	S
Dynamic cl	naracteristics		l			
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = -10 V; $I_{D}$ = -2.5 A; $V_{GS}$ = -4.5 V;	-	5	7.5	nC
$Q_{GS}$	gate-source charge	T <sub>j</sub> = 25 °C	-	0.7	-	nC
$Q_{GD}$	gate-drain charge		-	0.9	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = -10 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	550	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	63	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	53	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = -10 V; $I_{D}$ = -2.5 A; $V_{GS}$ = -4.5 V;	-	6	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega$ ; $T_j = 25 °C$	-	14	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	120	-	ns
t <sub>f</sub>	fall time		-	50	-	ns
Source-dra	in diode		I	1	1	
$V_{SD}$	source-drain voltage	I <sub>S</sub> = -1.2 A; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	-	-0.9	-1.2	V

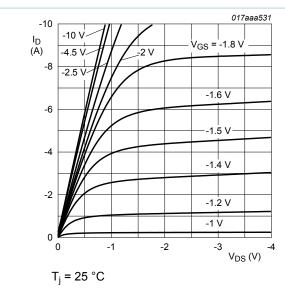


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

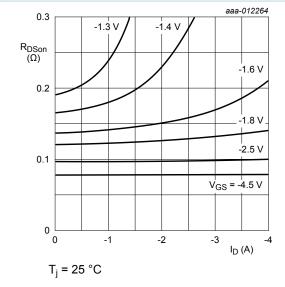


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

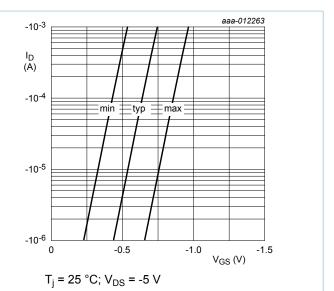


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

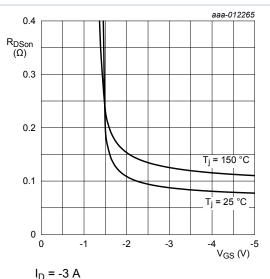


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

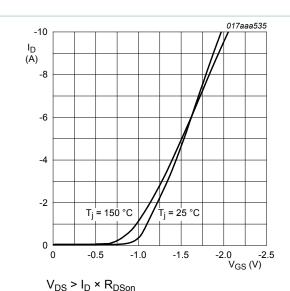


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

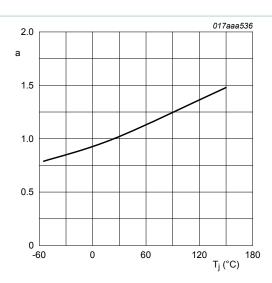


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

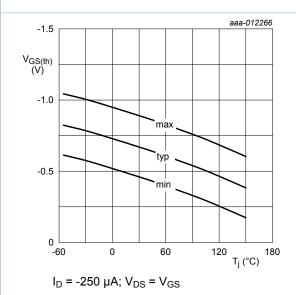


Fig. 12. Gate-source threshold voltage as a function of junction temperature

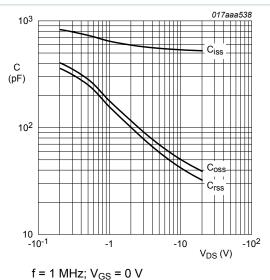


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

#### 20 V, P-channel Trench MOSFET

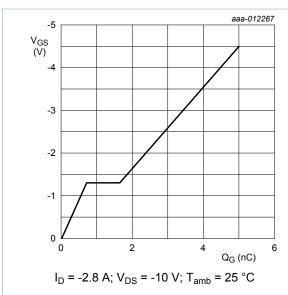


Fig. 14. Gate-source voltage as a function of gate charge; typical values

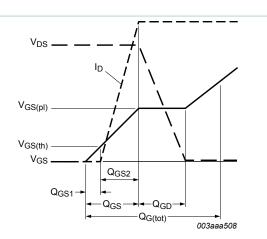


Fig. 15. MOSFET transistor: Gate charge waveform definitions

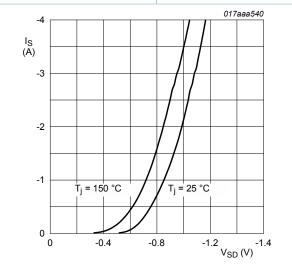
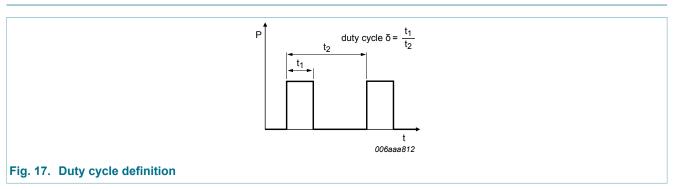


Fig. 16. Source current as a function of source-drain voltage; typical values

## 11. Test information

 $V_{GS} = 0 V$ 



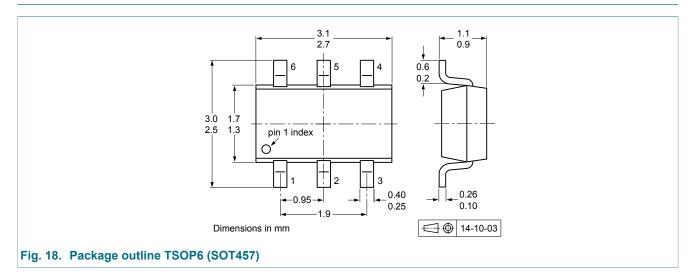
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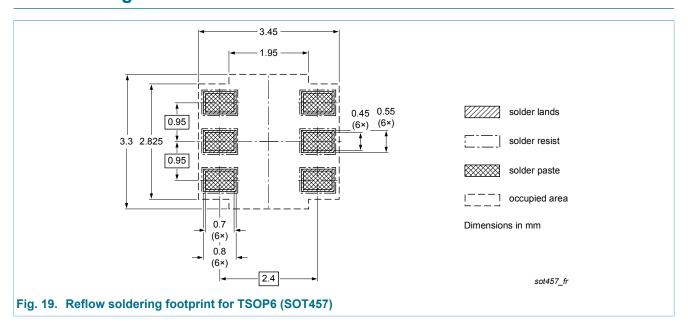
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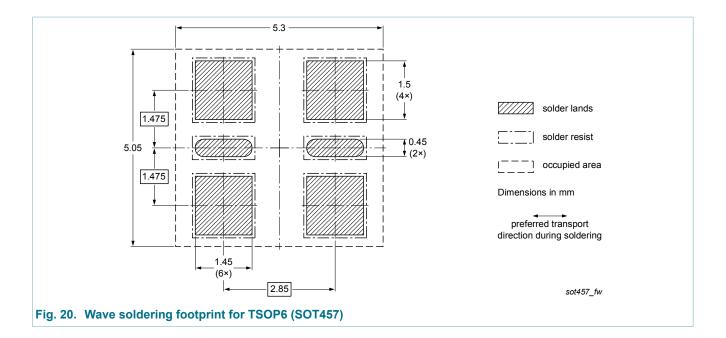
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## 12. Package outline



## 13. Soldering





20 V, P-channel Trench MOSFET

# 14. Revision history

#### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMN70XP v.1	20160129	Product data sheet	-	-

#### 20 V, P-channel Trench MOSFET

### 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
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#### 20 V, P-channel Trench MOSFET

## 16. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	3
9	Thermal characteristics	5
10	Characteristics	7
11	Test information	10
12	Package outline	11
13	Soldering	11
14	Revision history	13
15	Legal information	14
15.1	Data sheet status	14
15.2	Definitions	14
15.3	Disclaimers	14
15.4	Trademarks	15

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